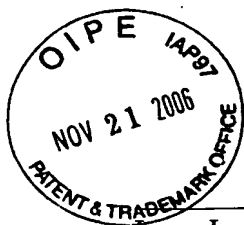


co/c



Docket No.: M4065.0909/P909-A  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:  
Li Li et al.

Patent No.: 7,126,179

Issued: October 24, 2006

For: A MEMORY CELL INTERMEDIATE  
STRUCTURE

**REQUEST FOR CERTIFICATE OF CORRECTION  
PURSUANT TO 37 CFR 1.322**

Attention: Certificate of Correction Branch  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**Certificate  
NOV 24 2006  
of Correction**

Dear Sir:

Upon reviewing the above-identified patent, Patentees noted typographical errors which should be corrected.

In Field (74) *Attorney, Agent, or Firm*-- on the patent cover:

"Dickstein ShapiroLL" should read --Dickstein Shapiro LLP--.

In the Other Publications portion of the References Cited section:

"Adler, D., Moss, S.C., Amorphous memories and bistable swithces, J. Vac. Sci. Technol. 9 (1972) 1182-89."

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The errors were not in the application as filed or amended by Applicants; accordingly no fee is required.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentees respectfully solicit the granting of the requested Certificate of Correction.

Dated: November 21, 2006

Respectfully submitted,

By



Thomas J. D'Amico

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DICKSTEIN SHAPIRO LLP  
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Attorney for Applicants

**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

Page 1 of 4

PATENT NO. : 7,126,179  
APPLICATION NO. : 10/758,102  
ISSUE DATE : October 24, 2006  
INVENTORS : Li Li et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

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